

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	11631	257/296,301-311,347,350,351.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/25 17:02
L2	113	257/908.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/25 17:03
L3	11664	1 or 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/25 17:03
L4	416	3 and (vertical adj transistor\$1)	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/25 17:30
L5	213	4 and ((isolat\$3 active) near (trench\$2 groove\$2 recess\$2))	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/25 17:28
L6	180	5 and ((body channel active) near (region area))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/25 17:29
L7	418	3 and (vertical adj transistor\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/25 17:28
L8	213	7 and ((isolat\$3 active) near (trench\$2 groove\$2 recess\$2))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/25 17:28
L9	180	8 and ((body channel active) near (region area))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/25 17:29

L10	1	array AND (vertical adj transistor\$1) AND substrate AND row\$1 AND (x near direction) AND column AND (y near direction) AND perpendicular AND trench\$2 AND isolat\$3 AND (active near region\$1) AND cell\$1 AND (charge near carrier) AND ((bottom lower) near (source drain)) AND ((top upper) near (source drain)) AND channel\$1 AND (gate near electrode) AND (gate near (oxide dielectric insulat\$3)) AND (layer near bod\$3).CLM.	US-PGPUB; USPAT	OR	ON	2005/10/25 17:51
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